NSN 5961-00-080-4834

Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-00-080-4834 **Inclosure Material:** Metal **Overall Length:** Between 0.320 inches and 0.468 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact **Electrode Internally-electrically Connected To Case:** Anode **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** Between 0.380 inches and 0.487 inches **Thread Size:** 0.190 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 100.0 breakover voltage, dc **Current Rating Per Characteristic:** 2.00 amperes forward current, average watts **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius ambient air **Special Features:** Junction pattern arrangement: pnpn **Thread Series Designator:** Unf **Terminal Type And Quantity:** 3 tab, solder lug and 1 threaded stud Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: A110a0